

CMPTH10

**SURFACE MOUNT
NPN SILICON
RF TRANSISTOR**



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPTH10 type is an NPN silicon RF transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for low noise UHF/VHF amplifier and high output oscillator applications.

MARKING CODE: C3E



SOT-23 CASE

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CB0} 30
 V_{CEO} 25
 V_{EBO} 3.0
 P_D 350
 T_J, T_{stg} -65 to +150
 θ_{JA} 357

UNITS

V
V
V
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

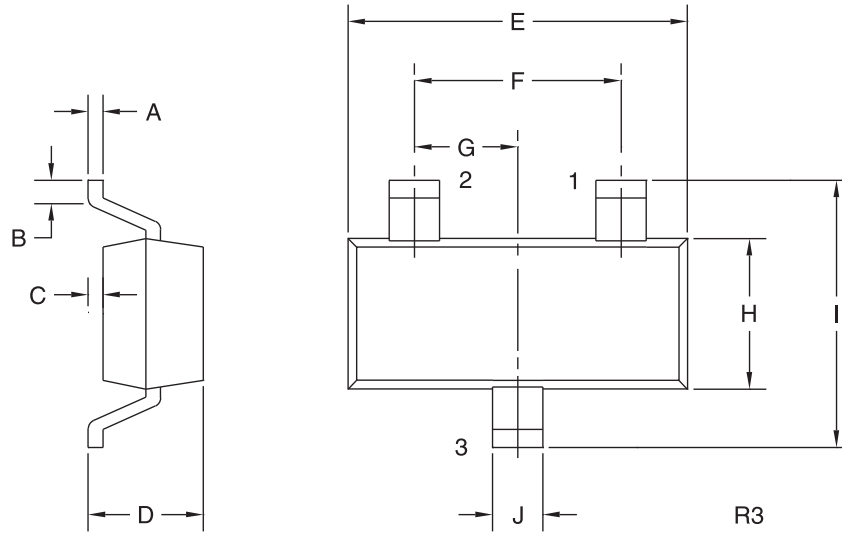
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=25V$		100	nA
I_{EBO}	$V_{EB}=2.0V$		100	nA
BV_{CBO}	$I_C=100\mu A$	30		V
BV_{CEO}	$I_C=1.0mA$	25		V
BV_{EBO}	$I_E=10\mu A$	3.0		V
$V_{CE(SAT)}$	$I_C=4.0mA, I_B=0.4mA$		0.50	V
$V_{BE(ON)}$	$V_{CE}=10V, I_B=4.0mA$		0.95	V
h_{FE}	$V_{CE}=10V, I_C=4.0mA$	60		
f_T	$V_{CE}=10V, I_C=4.0mA, f=100MHz$	650		MHz
C_{cb}	$V_{CB}=10V, I_E=0, f=1.0MHz$		0.70	pF
C_{rb}	$V_{CB}=10V, I_E=0, f=1.0MHz$		0.65	pF
$rb'C_c$	$V_{CB}=10V, I_C=4.0mA, f=31.8MHz$		9.0	ps

R5 (3-February 2010)

CMPH10
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 NPN SILICON
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SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

MARKING CODE: C3E

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R5 (3-February 2010)